

THE KENYA POLYTECHNIC

ELECTRICAL/ELECTRONICS ENGINEERING

DEPARTMENT

HIGHER DIPLOMA IN ELECTRICAL ENGINEERING

END OF YEAR II EXAMINATIONS

NOVEMBER 2006

DIGITAL ELECTRONICS

3 HOURS

INSTRUCTIONS TO CANDIDATES:

You should have the following for this examination:

Answer booklet

Calculator/Mathematical tables

Answer any FIVE of the following EIGHT questions.

All questions carry equal marks and the maximum marks for each part of a question are as shown.

This paper consists of 5 printed pages.

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1. (a) Define the following terms with reference to Karnaugh maps:
- (i) Prime implicant
 - (ii) Essential prime implicant
 - (iii) Non-essential prime implicant (3 marks)
- (b) Determine the minimum sum of products solution for the function:
- $$F(A, B, C, D) = \Sigma m(0,1,3,5,6,7,8,10,14,15) \quad (8 \text{ marks})$$
- (c) Using a five-variable K-map, simplify the function:
- $$F(A, B, C, D, E) = \pi(1,3,5,7,8,10,12,14,16,18,19,20,22,23,24,26,28,30) \text{ in:}$$
- (i) Sum of products
 - (ii) Product of sums (9 marks)
2. (a) (i) Express the Boolean function $F = AB + \bar{A}C$ in a product of maxterm form.
- (ii) Using the result in (a)(i) or otherwise, obtain the expression for the sum of minterms for the function. (7 marks)
- (b) Use Boolean algebra to show that an X-OR function, F , with four variables is made up of the indicated minterms.
- $$F(A, B, C, D) = \Sigma M(1,2,4,7,8,11,13,14) \quad (5 \text{ marks})$$
- (c) Using double complement method, use NOR gates only to realize the function $F = A(B + CD) + \bar{B}\bar{C}$ (8 marks)
3. (a) Using AND and OR gates, find a minimum network to realize:
- $$F(A, B, C, D) = M_0 M_1 M_3 M_{13} M_{14} M_{15}$$
- (i) Using two logic level
 - (ii) Using three logic level
- [Number of gates and gate inputs are the design parameters] (10 marks)
- (b) (i) Find the minimum network of two-input AND and two-input OR gates to realize: $F(A, B, C, D) = \Sigma m(0,1,2,3,4,5,7,9,11,13,14,15)$
- (ii) Convert the network in (b)(i) to two-input NAND gate using direct polarity notation. Add inverters where necessary. Assume that only A(L), B(H), C(L) and D(H) are available as inputs and that the output should be F(H). (10 marks)
4. (a) (i) Explain how a decoder can be used for memory address decoding.

- (ii) A ROM has n input lines and m output lines. Write down the expression for the capacity of the ROM. (6 marks)
- (b) (i) Draw the logic diagram of a 4-to-1 multiplexer.
(ii) Explain the operation of the multiplexer in (b)(i). (8 marks)
- (c) Implement the function $F(A, B, C) = \Sigma(1,3,5,6)$ with a 4x1 MUX with:
(i) B and C connected to the selection lines S_1 and S_0 respectively.
(ii) A and B connected to the selection lines S_1 and S_0 respectively. (6 marks)
5. (a) Distinguish between synchronous and asynchronous logic. (2 marks)
(b) (i) Design a counter that has a repeated sequence of six states as listed in table 1. [Use J-K flip-flops]

Count Sequence

A	B	C
0	0	0
0	0	1
0	1	0
1	0	0
1	0	1
<u>1</u>	<u>1</u>	<u>0</u>

Table 1

- (ii) By use of a state diagram, show that the counter in (b)(i) is self-starting. (10 marks)
- (c) A combinational circuit is defined by the functions:
 $F_1(A, B, C) = \Sigma(3,5,6,7)$
 $F_2(A, B, C) = \Sigma(0,2,4,7)$
- Implement the circuit with a PLA having three inputs, four product terms and two outputs. (8 marks)
6. (a) Compare any TWO characteristics of a practical operational amplifier to that of ideal one. (2 marks)

(b) (i) Figure 1 shows a binary weighted resistor D/A converter. Show that the:

I. Output resistance is independent of the digital word and

that $R_0 = \frac{2^{N-1}}{2^N - 1} R$

II. Analog output voltage for the MSB is $V_0 = \frac{2^{N-1}}{2^N - 1} U_R$

III. Analog output voltage for the least significant bit is

$$V_0 = \frac{1}{2^N - 1} V_R$$

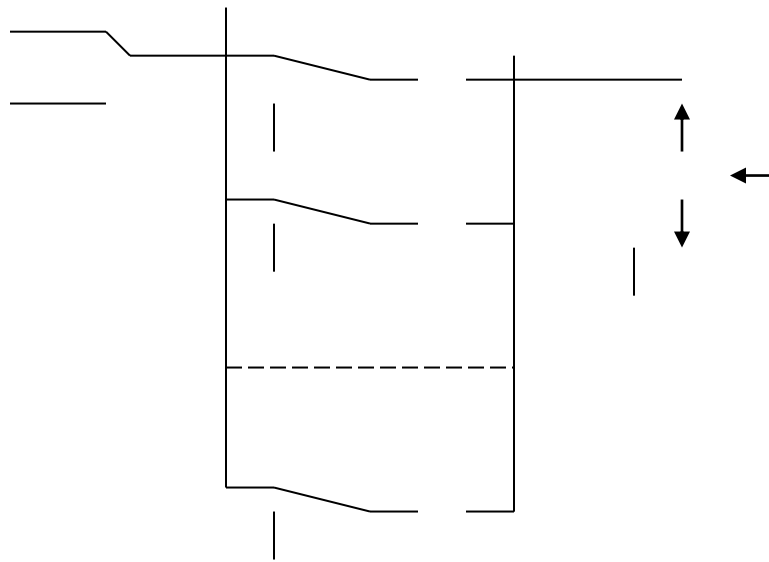


Figure 1

(ii) Explain the main disadvantage of the binary weighted ladder.

(12 marks)

(c) Figure 2 shows a R-2R D/A converter network.

